

ABSTRACT

A semiconductor storage device according to an embodiment includes a substrate, a transistor, a multi-layered body, a pillar, and a source line. The transistor is provided on the substrate. The multi-layered body includes a plurality of gate electrode
5 layers and a plurality of insulating layers alternately stacked one by one in a first direction. The pillar includes an insulating core, a channel layer, and a memory film. The source line is disposed between the multi-layered body and the substrate. The source line extends at least in a second direction. The pillar has a first end and a second end. The first end is in contact with the source line. The second end is positioned on a
10 side opposite to the first end in the first direction. A width of the first end in the second direction is larger than a width of the second end in the second direction.